

# EVVOSEMI<sup>®</sup>

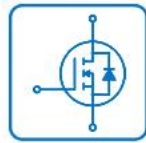
THINK CHANGE DO



ESD



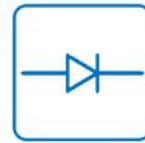
TVS



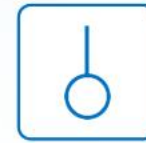
MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

▶ Domestic	Part Number	BU2508AF
▶ Overseas	Part Number	BU2508AF
▶ Equivalent	Part Number	BU2508AF

EV is the abbreviation of name EVVO

## Silicon NPN Power Transistor

### DESCRIPTION

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 700V$  (Min)
- High Switching Speed

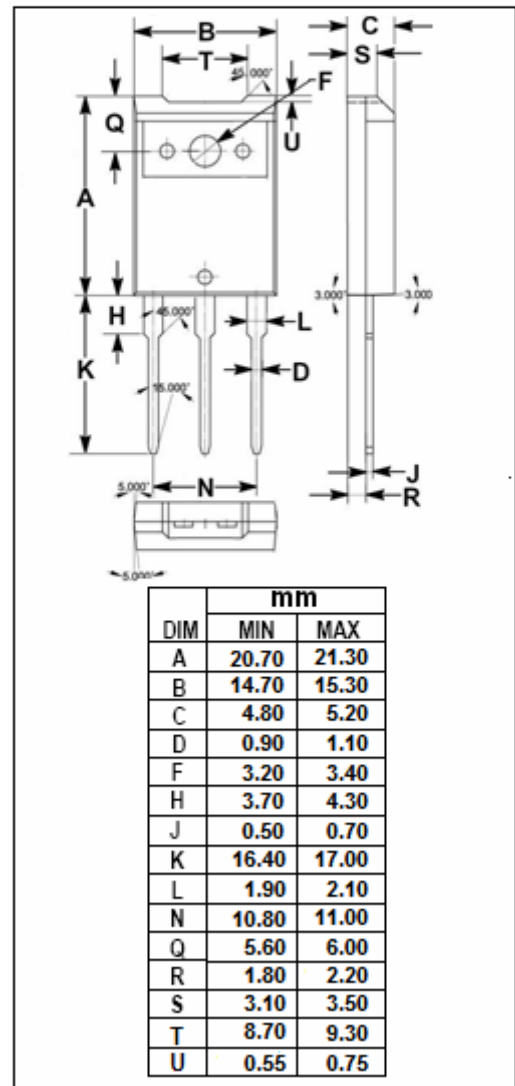
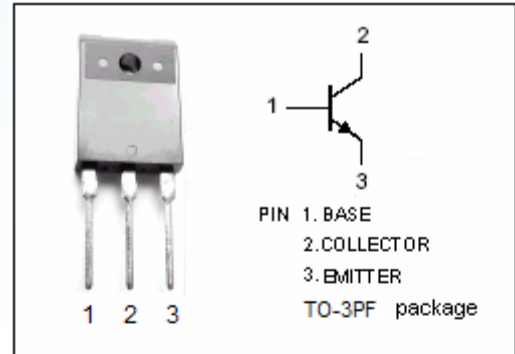
### APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector- Emitter Voltage( $V_{BE} = 0$ )	1500	V
$V_{CEO}$	Collector-Emitter Voltage	700	V
$V_{EBO}$	Emitter-Base Voltage	7.5	V
$I_C$	Collector Current- Continuous	8	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current- Continuous	4	A
$I_{BM}$	Base Current-Peak	6	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	45	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ C$

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.5	$^\circ C/W$

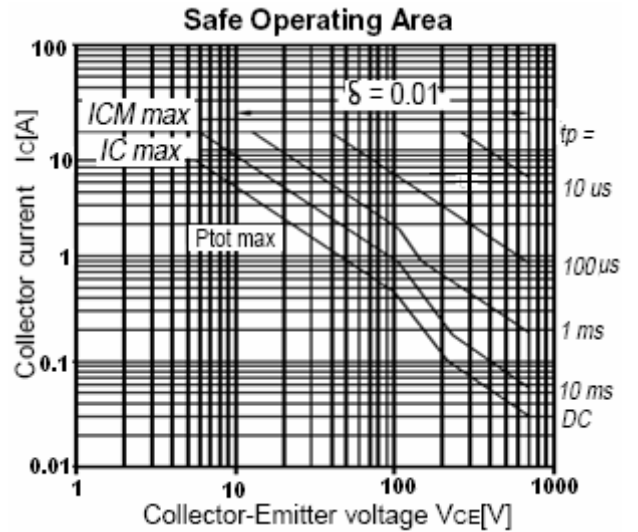
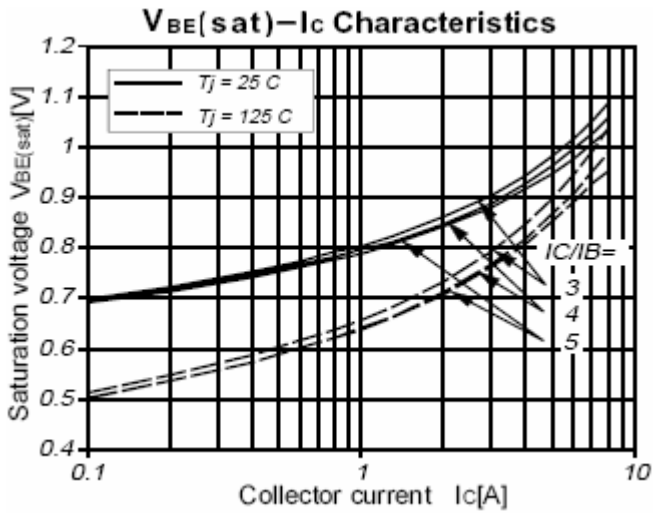
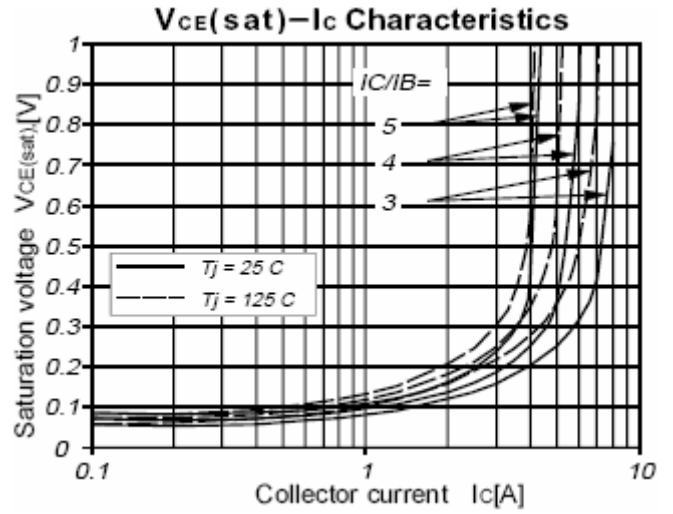
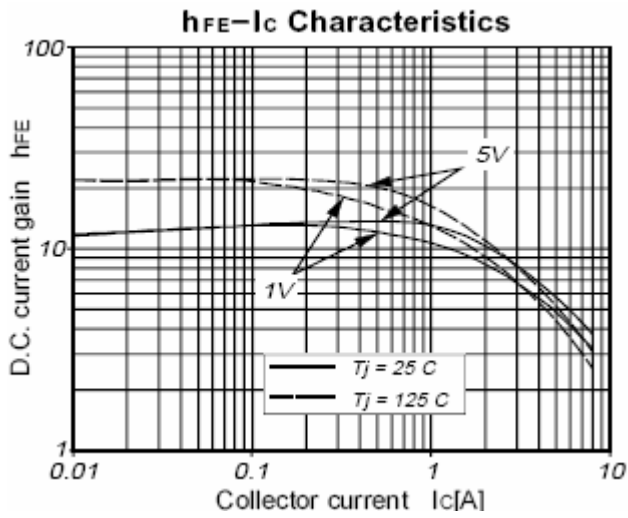


**ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100mA ; I <sub>B</sub> = 0, L= 25mH	700			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7.5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.1A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.7A			1.1	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V ; V <sub>BE</sub> = 0 V <sub>CE</sub> = 1500V ; V <sub>BE</sub> = 0; T <sub>C</sub> =125°C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7.5V ; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A ; V <sub>CE</sub> = 5V		13		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4.5A ; V <sub>CE</sub> = 1V	4		7	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		80		pF

## Switching times

t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 4.5A , I <sub>B(end)</sub> = 1.1A; L <sub>B</sub> = 6 μ H -V <sub>BB</sub> = 4V; (-dI <sub>B</sub> /dt= 0.6A/ μ s)			6.0	μ s
t <sub>f</sub>	Fall Time				0.6	μ s



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